

High purity silicon carbide powders for semiconductor and electronic applications.

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications.

Size

Char. description	Unit	Lower Limit	Upper Limit
Sieve 50 (300µm)	%	-	0
Sieve 100 (150µm)	%	-	4
Sieve 120 (125µm)	%	12	22
Sieve 140 (106µm)	%	17	27
Sieve 200 (75µm)	%	30	40
Sieve 325 (45µm)	%	15	28
Sieve -325 (-45µm)	%	-	3

Typical Chemistry

Char. description	Unit	Lower Limit	Upper Limit
Free C	%	-	0,06
Total O2	%	-	0,10
Free Si	%	-	0,10
Fe	ppm	-	400
Al	ppm	-	400
Ni	ppm	-	75
V	ppm	-	50
Ca	ppm	-	60
Ti	ppm	-	100
Zr	ppm	-	20

Analytical Procedures: All measurement is in accordance to FEPA, ANSI or JIS, or other methods in agreement with customers.

Packaging: 25 kg paper bags